



### Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$

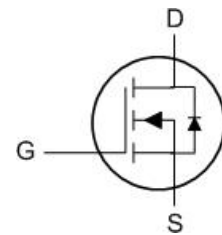
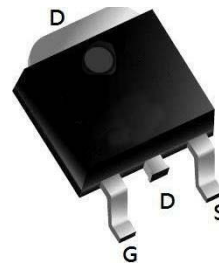
### Product Summary

BVDSS	RDSON	ID
120V	6.0 mΩ	120A

### Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

### TO252 Pin Configuration



### Absolute Maximum Ratings:

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	120	V
$I_D$	Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	120
	Continuous Drain Current	$T_C = 100\text{ }^\circ\text{C}$	79
$I_{DM}^{a1}$	Pulsed Drain Current	500	A
$E_{AS}^{a2}$	Single pulse avalanche energy	326	mJ
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$P_D$	Power Dissipation	227	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^\circ\text{C}$

### Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.55	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	60	$^\circ\text{C}/\text{W}$

**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified) :

<b>Static Characteristics</b>						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$V_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	120	--	--	V
$I_{DSS}$	Drain to Source Leakage Current	$V_{DS} = 120V, V_{GS}= 0V$	--	--	1	$\mu A$
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS} = +20V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS} = -20V$	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D = 250\mu A$	2.5	3	3.5	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=20A$	--	6	7.5	$m\Omega$

<b>Dynamic Characteristics</b>						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 60V$ $f = 1.0MHz$	--	3614	--	pF
$C_{oss}$	Output Capacitance		--	423	--	
$C_{rss}$	Reverse Transfer Capacitance		--	12	--	
$R_g$	Gate resistance		--	0.84	--	$\Omega$

<b>Resistive Switching Characteristics</b>						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D = 20A$ $V_{DS} = 60V$ $V_{GS} = 10V$ $R_G = 5\Omega$	--	20	--	ns
$t_r$	Rise Time		--	65	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	32	--	
$t_f$	Fall Time		--	49	--	
$Q_g$	Total Gate Charge	$V_{GS} = 0\sim 10V$	--	60.8	--	nC
$Q_{gs}$	Gate Source Charge	$V_{DS} = 90V$	--	18.8	--	
$Q_{gd}$	Gate Drain Charge	$I_D = 20A$	--	14.7	--	

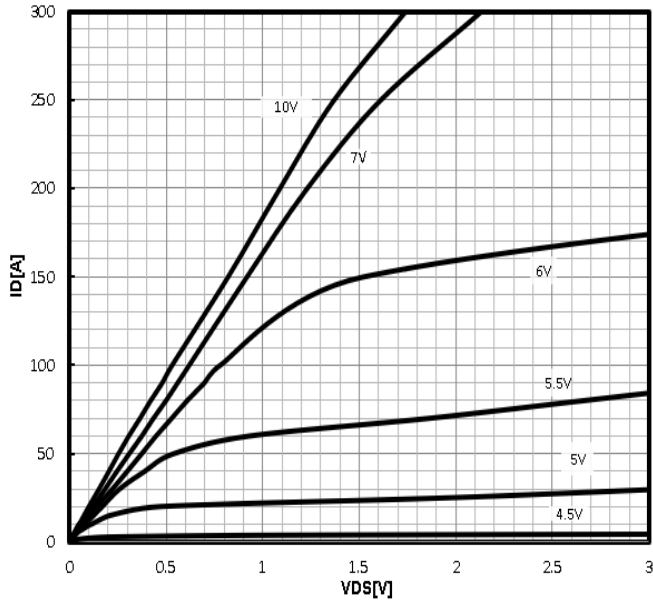
<b>Source-Drain Diode Characteristics</b>						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$I_S$	Diode Forward Current	$T_C = 25^\circ C$	--	--	120	A
$V_{SD}$	Diode Forward Voltage	$I_S=20A, V_{GS}=0V$	--	0.83	1.2	V
$t_{rr}$	Reverse Recovery time	$I_S=40A,$ $dI/dt=100A/\mu s$	--	70	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	129	--	nC

 $a_1$  : Repetitive rating; pulse width limited by maximum junction temperature

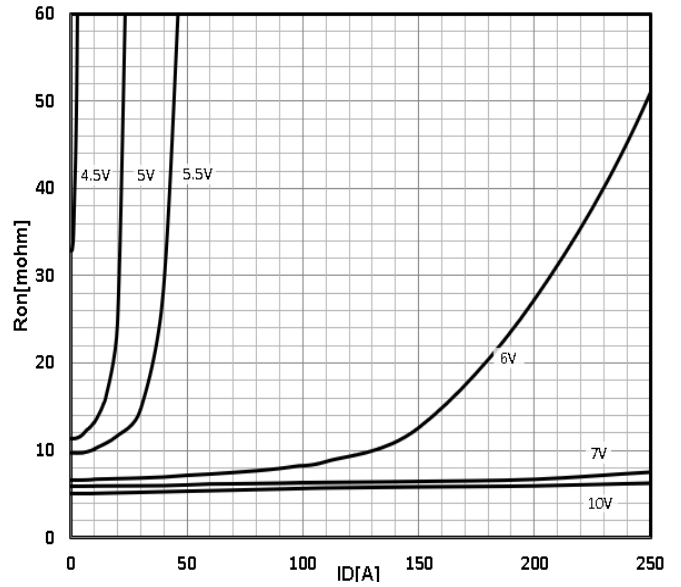
 $a_2$  :  $V_{DD}=60V, L=0.5mH, R_g=25\Omega, \text{Starting } T_J=25^\circ C$

**Characteristics Curve:**

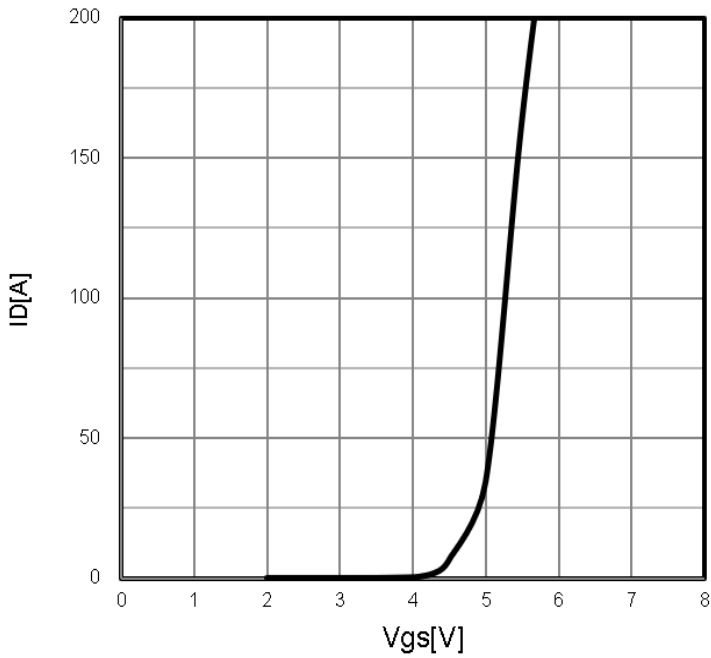
**Typ. output characteristics**  
 $I_D=f(V_{DS})$



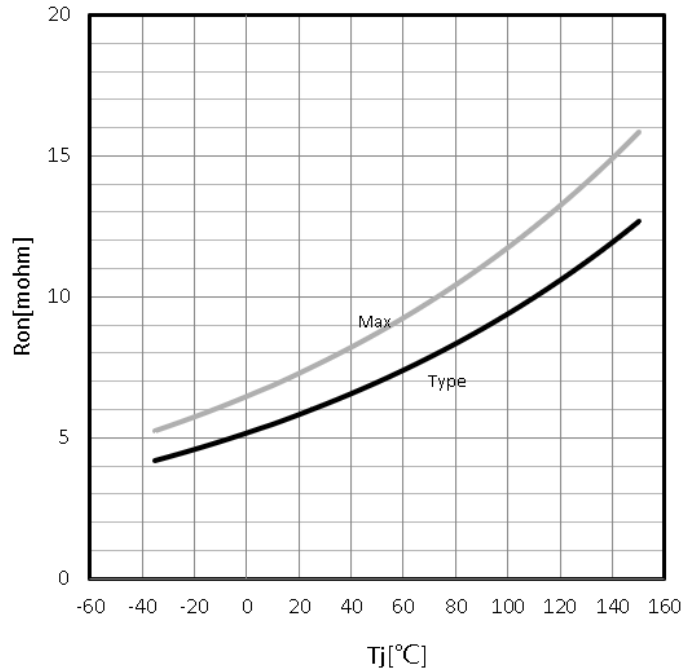
**Typ. drain-source on resistance**  
 $R_{DS(on)}=f(I_D)$



**Typ. transfer characteristics**  
 $I_D=f(V_{GS})$

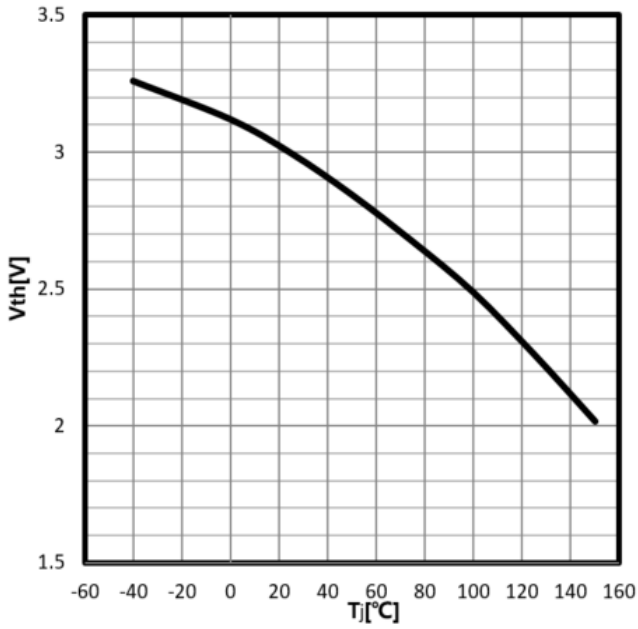


**Drain-source on-state resistance**  
 $R_{DS(on)}=f(T_j); I_D=20A; V_{GS}=10V$



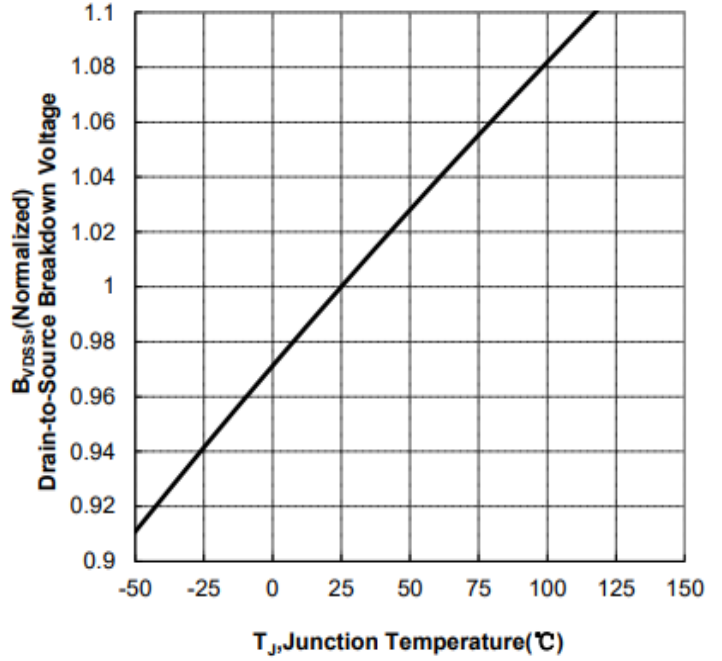
**Gate Threshold Voltage**

$V_{TH}=f(T_j); I_D=250\mu A$



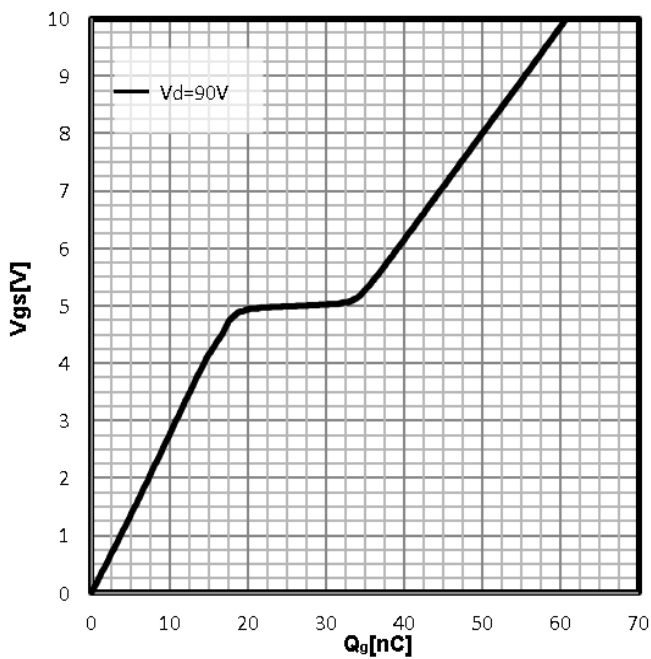
**Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=250\mu A$



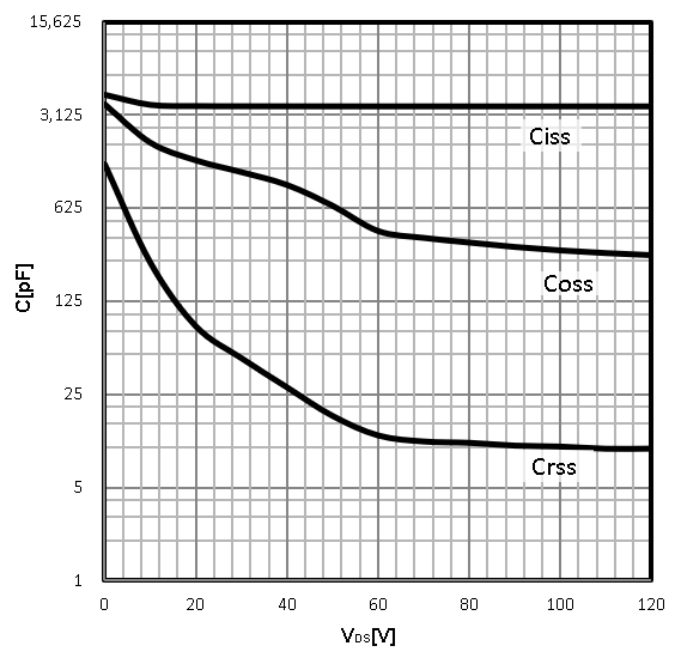
**Typ. gate charge**

$V_{GS}=f(Q_{gate})$

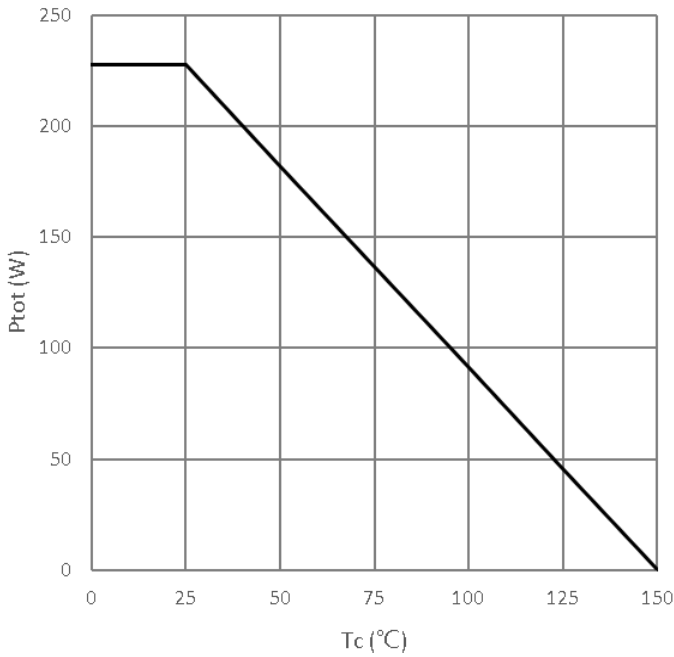


**Typ. capacitances**

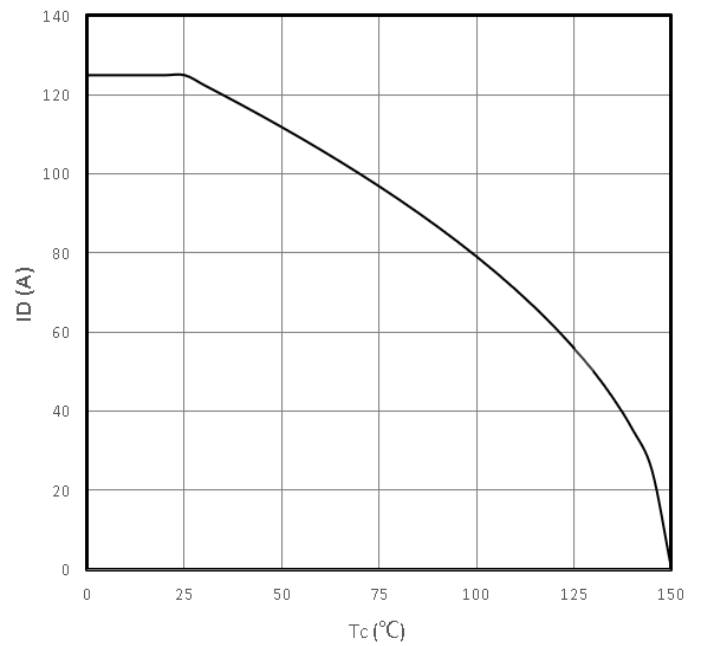
$C=f(V_{DS}); V_{GS}=0V; f=1MHz$



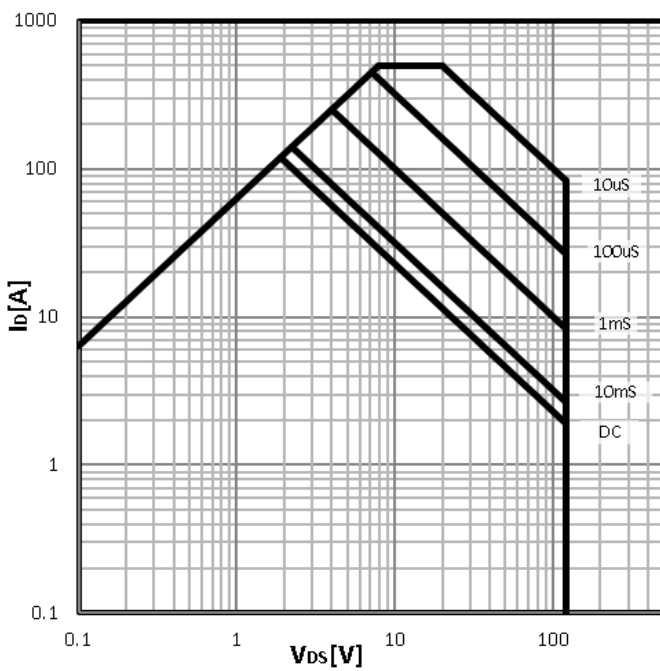
**Power Dissipation**  
 $P_{tot}=f(T_j)$



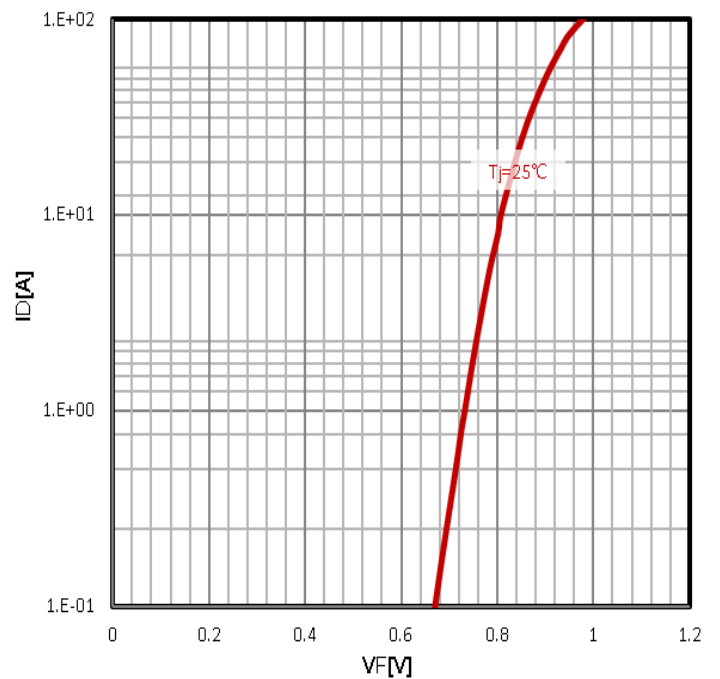
**Maximum Drain Current**  
 $I_D=f(T_c)$



**Safe operating area**  
 $I_D=f(V_{DS})$

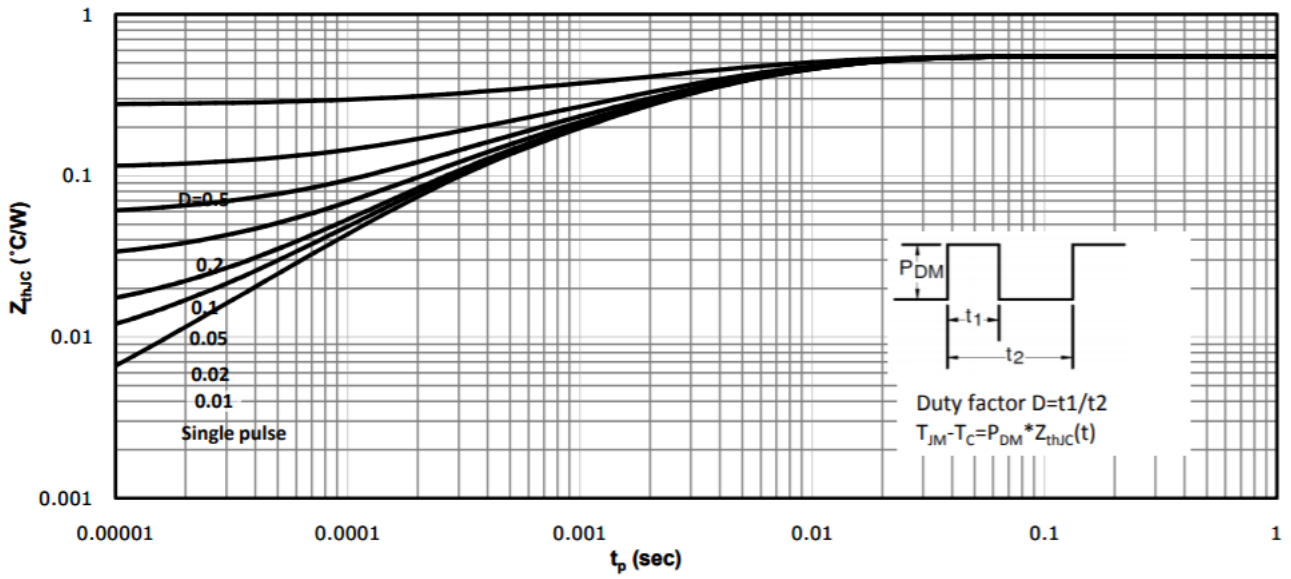


**Body Diode Forward Voltage Variation**  
 $I_F=f(V_{GS})$

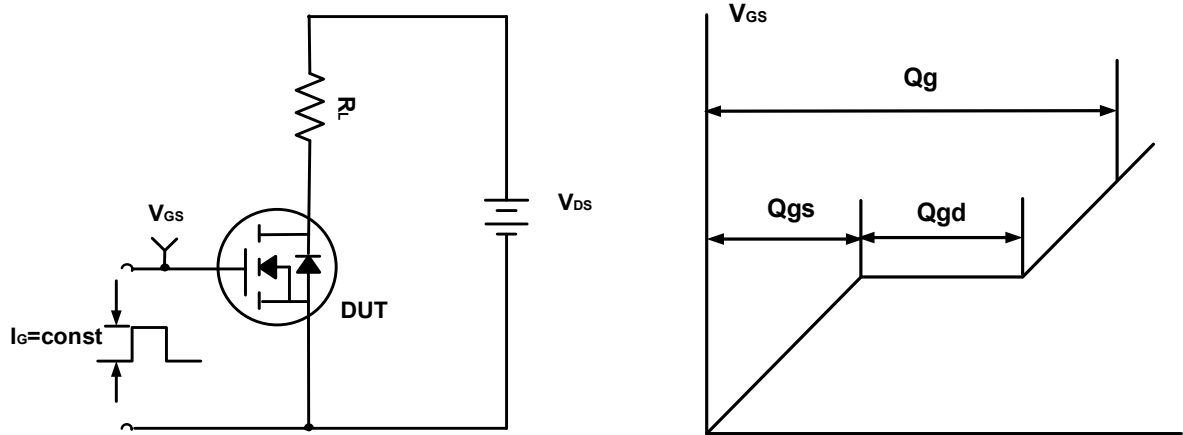


**Max. transient thermal impedance**

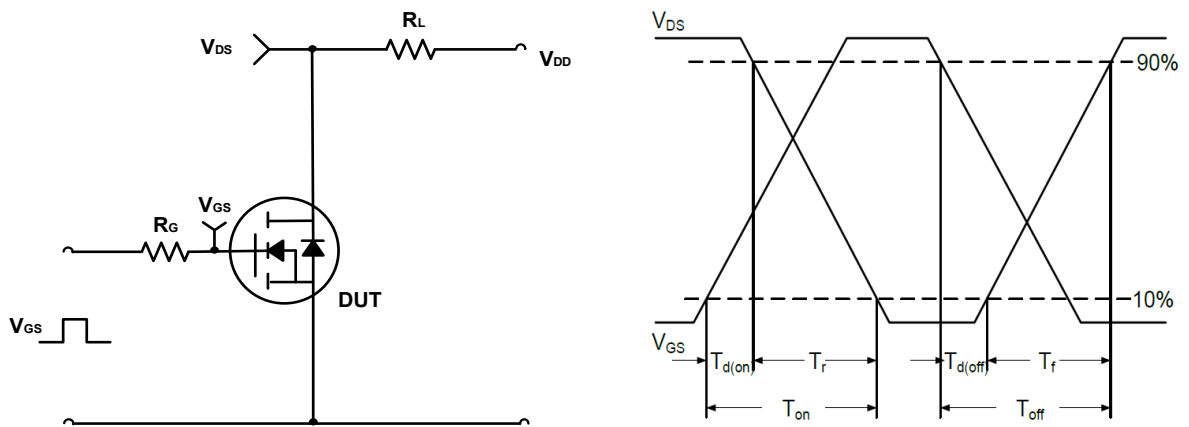
$$Z_{thJC} = f(t_p)$$



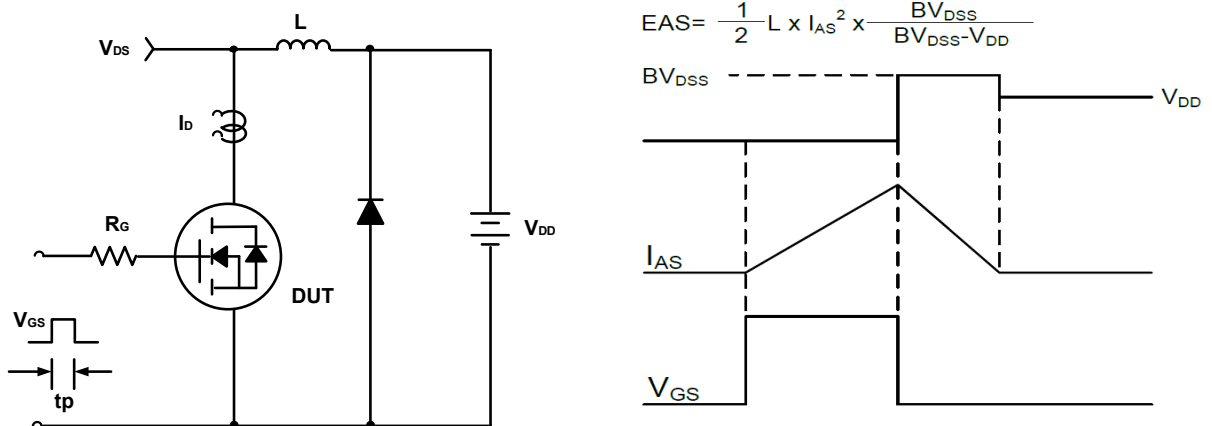
**Test Circuit**



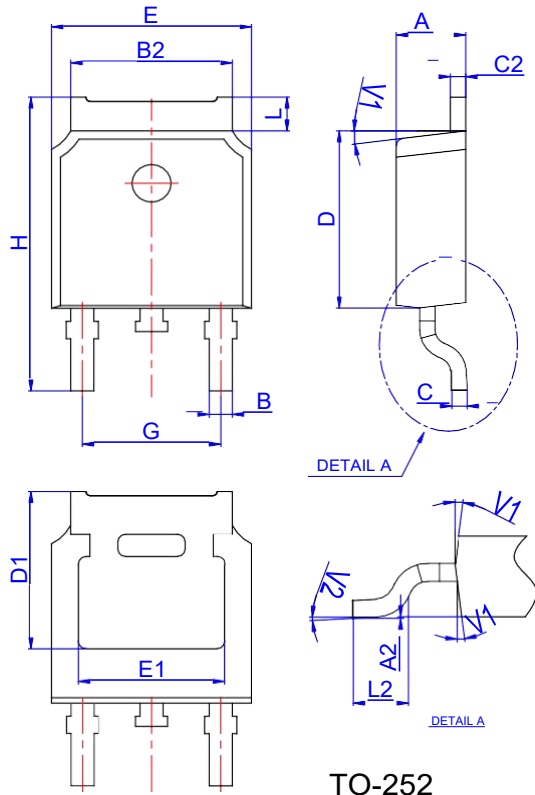
**Figure A. Gate Charge Test Circuit & Waveforms**



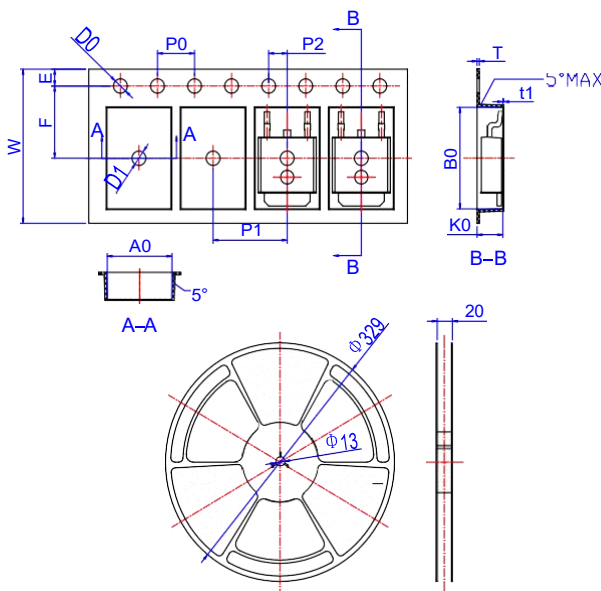
**Figure B. Switching Test Circuit & Waveforms**



**Figure C. Unclamped Inductive Switching Circuit & Waveforms**

**Package Mechanical Data TO 252**

**TO-252**

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**Reel Specification-TO-252-4R**


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583